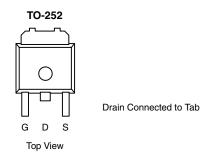


SUD50N02-06P N-Channel

20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a			
20	0.0060 at V _{GS} = 10 V	26			
20	0.0095 at V _{GS} = 4.5 V	21			



Ordering Information: SUD50N02-06P-E3 (Lead (Pb) free)

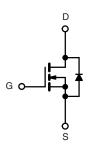
FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized for High Efficiency
- 100 % R_q Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT

APPLICATIONS

- Synchronous Buck DC/DC Conversion
 - Desktop
 - Server



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	20	V		
Gate-Source Voltage		V _{GS}	± 20	V		
Outline Paris Outline	T _A = 25 °C	I-	26 ^a			
Continuous Drain Current ^a	T _C = 25 °C	I _D	50 ^b			
Pulsed Drain Current		I _{DM}	100	Α		
Continuous Source Current (Diode Conduction) ^a		I _S	26			
Avalanche Current	L = 0.1 mH	I _{AS}	45			
Single Pulse Avalanche Energy	L = 0.1 IIII1	E _{AS}	101	mJ		
Maximum Power Dissipation	T _A = 25 °C	P _D	6.8 ^a	W		
Maximum Fower Dissipation	T _C = 25 °C] 'D [65] "		
Operating Junction and Storage Temperature Range	·	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifesture Ituration to Ameliant	t ≤ 10 s	- R _{thJA}	18	22	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		40	50		
Maximum Junction-to-Case		R _{thJC}	1.9	2.3		

Notes:

- a. Surface mounted on FR4 board, $t \le 10$ s.
- b. Limited by package.



SUD50N02-06P N-Channel

20 V (D-S) 175 °C MOSFET

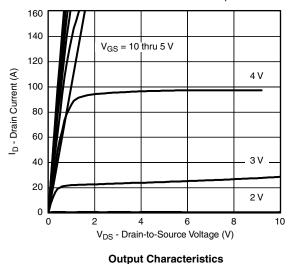
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					l L		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V	
Gate Threshold Voltage	V _{GS(th)}				3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1 μA		
Zero date voltage Brain Garrent	.055	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50	μΑ	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		0.0046	0.006		
Drain-Source On-State Resistance ^b	r _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125 \text{ °C}$			0.0084	Ω	
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0073	0.0095		
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$	15			S	
Dynamic ^a							
Input Capacitance	C _{iss}			2550		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$		900			
Reverse Transfer Capacitance	C _{rss}			415			
Total Gate Charge ^c	Q_g			19	30		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 50 \text{ A}$		7.5		nC	
Gate-Drain Charge ^c	Q _{gd}			6			
Gate Resistance	R_g		0.5	1.5	2.4	Ω	
Turn-On Delay Time ^c	t _{d(on)}			11	20		
Rise Time ^c	t _r	$V_{DD} = 10 \text{ V}, R_{L} = 0.2 \Omega$		10	15	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		24	35	115	
Fall Time ^c	t _f			9	15		
Source-Drain Diode Ratings and Cha	racteristic (T	C = 25 °C)					
Pulsed Current	I _{SM}				100	Α	
Diode Forward Voltage ^b	V_{SD}	I _F = 50 A, V _{GS} = 0 V		1.2	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, dl/dt = 100 A/μs		35	70	ns	

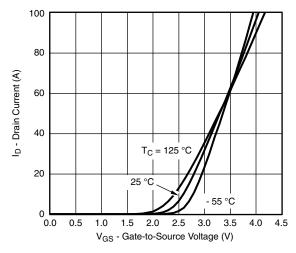
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C unless noted)





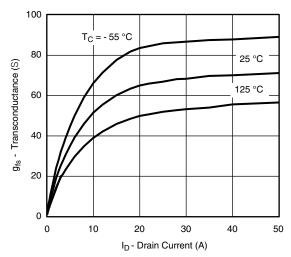
Transfer Characteristics



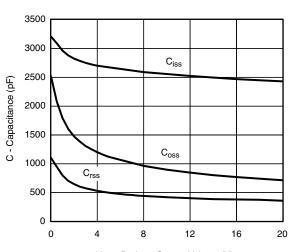
SUD50N02-06P

N-Channel 20 V (D-S) 175 °C MOSFET

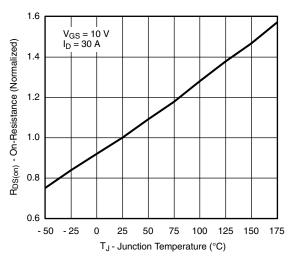
TYPICAL CHARACTERISTICS (25 °C unless noted)



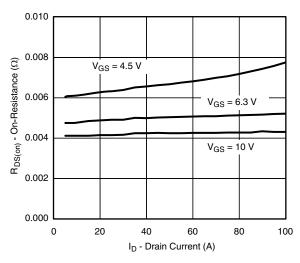
Transconductance



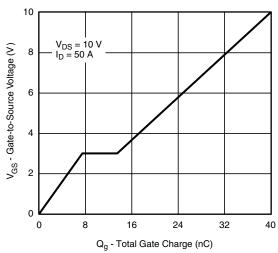
 V_{DS} - Drain-to-Source Voltage (V) $\label{eq:capacitance}$



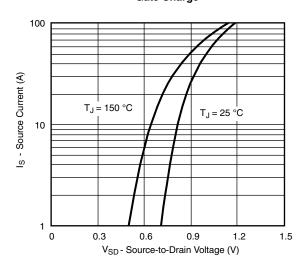
On-Resistance vs. Junction Temperature



On-Resistance vs. Drain Current



Gate Charge

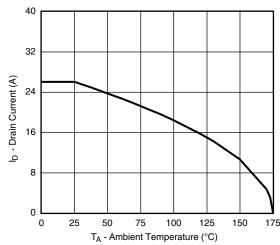


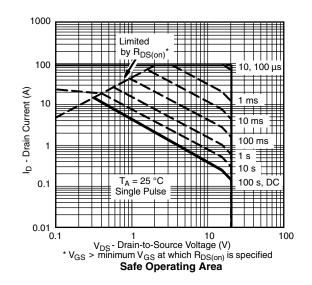
Source-Drain Diode Forward Voltage

SUD50N02-06P

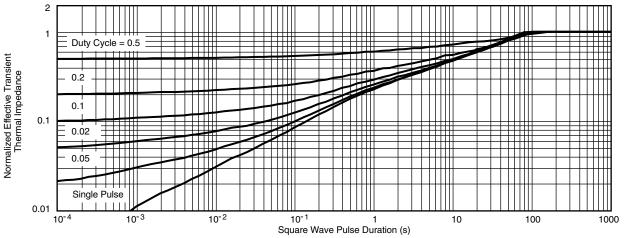
N-Channel 20 V (D-S) 175 °C MOSFET

THERMAL RATINGS

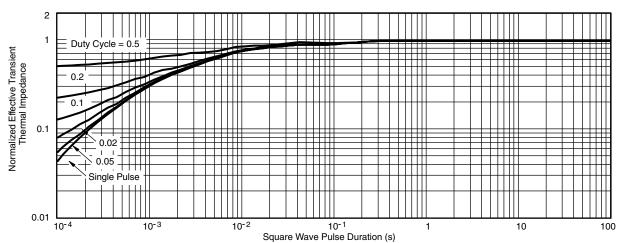










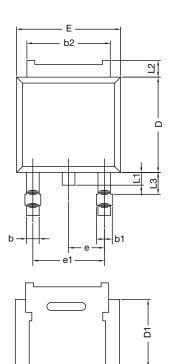


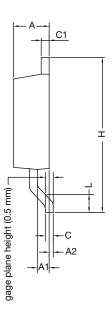
Normalized Thermal Transient Impedance, Junction-to-Case

SUD50N02-06P

N-Channel 20 V (D-S) 175 °C MOSFET

TO-252AA CASE OUTLINE





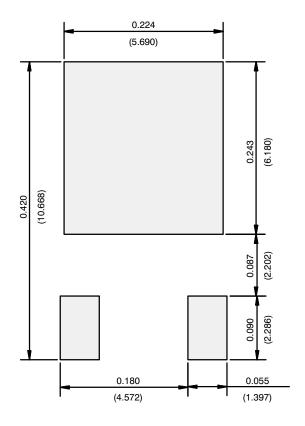
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090	BSC	
e1	4.57	BSC	0.180	BSC	
Η	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

SUD50N02-06P N-Channel 20 V (D-S) 175 °C MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



SUD50N02-06P N-Channel 20 V (D-S) 175 °C MOSFET

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

freestyle Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on it s or their behalf (collectively, "freestyle"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

freestyle makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vi shay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain type s of applications are based on freestyle's knowledge of typical requirements that are often placed on freestyle products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specification s may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify freestyle's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, freestyle products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the freestyle product could result in personal injury or death. Customers using or selling freestyle products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold freestyle and its distributors harmless from and against an y and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vis hay

Material Category Policy

freestyle Intertechnology, Inc. hereby certi fies that all its products that are id entified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some freestyle documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002 /95/EC conform to Directive 2011/65/EU.